

描述 / Descriptions

PDFN3×3A-8L 塑封封装 P 沟道 MOS 场效应管。

P-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

特征 / Features

$V_{DS} (V) = -16V$ $I_D = -49.5A$ ($V_{GS} = \pm 12V$)

$R_{DS(ON)} @ -4.5V \leq 8m\Omega$ (Typ. $6.6m\Omega$)

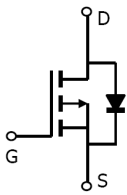
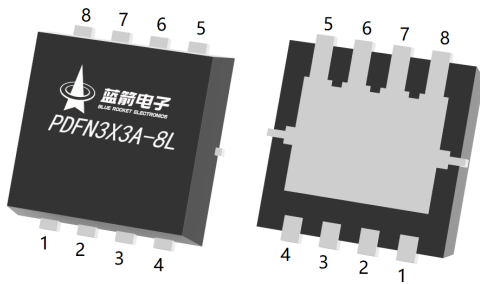
$R_{DS(ON)} @ -2.5V \leq 15m\Omega$ (Typ. $9.8m\Omega$)

无卤产品。HF Product.

用途 / Applications

笔记本交流输入负载开关，电池保护充电/放电。

Notebook AC-in load switch, Battery protection charge/discharge.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

出脚	定义
Pin1	S
Pin2	S
Pin3	S
Pin4	G
Pin5	D
Pin6	D
Pin7	D
Pin8	D

印章代码 / Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V _{DS}	-16	V
Drain Current - Continuous		I _D (T _c =25°C)	-49.5	A
Drain Current - Continuous		I _D (T _c =100°C)	-33	A
Drain Current – Pulsed		I _{DM}	-132	A
Gate-Source Voltage		V _{GS}	± 12	V
Power Dissipation		P _D (T _c =25°C)	27.5	W
Power Dissipation		P _D (T _c =100°C)	11	W
Single Pulse Avalanche Energy(L=0.5mH)		E _{AS}	160	mJ
Avalanche Current		I _{AS}	-15.5	A
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C
Thermal resistance, junction - ambient	t ≤ 10s	R _{θJA}	27	°C/ W
	Steady-State		60	
Thermal resistance, junction - case	Steady-State	R _{θJC}	4.55	

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu\text{A}$ $V_{GS}=0\text{V}$	-16	-18.5		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-12.8\text{V}$ $V_{GS}=0\text{V}$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu\text{A}$	-0.5	-0.76	-1.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5\text{V}$, $I_D=-15\text{A}$		6.6	8	m Ω
		$V_{GS}=-2.5\text{V}$, $I_D=-10\text{A}$		9.8	15	
		$V_{GS}=-1.8\text{V}$, $I_D=-5\text{A}$		18		
Diode Forward Voltage	V_{SD}	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$			-1.2	V
Reverse Recovery Time	t_{rr}	$V_{DS}=-10\text{V}$, $I_D=-14\text{A}$		2.9		ns
Reverse Recovery Charge	Q_{rr}	$dI_{SD}/dt = 100\text{ A}/\mu\text{s}$		8		nC
Input Capacitance	C_{iss}	$V_{DS}=-15\text{V}$ $V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		2620		pF
Output Capacitance	C_{oss}			440		
Reverse Transfer Capacitance	C_{rss}			375		
Gate resistance	R_g	$V_{GS}=0\text{V}$ $V_{DS}=0\text{V}$ $f=1\text{MHz}$		7.8		Ω

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Total Gate Charge	Q_g	$V_{GS}=-4.5V, \quad V_{DS}=-10V,$ $I_D=-14A$		26.5		nC
Gate Source Charge	Q_{gs}			2.4		
Gate Drain Charge	Q_{gd}			9.7		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-4.5V \quad V_{DS}=-10V$ $I_D=-14A \quad R_G=3\Omega$		15.7		ns
Turn-On Rise Time	t_r			116		
Turn-Off Delay Time	$t_{d(off)}$			86.1		
Turn-Off Fall Time	t_f			121		

电参数曲线图 / Electrical Characteristic Curve

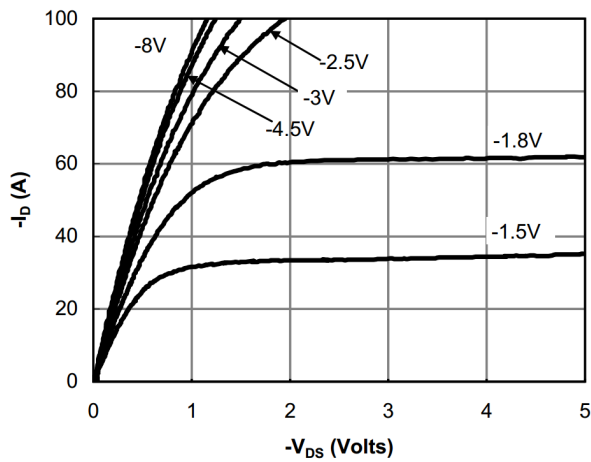


Fig 1: On-Region Characteristics

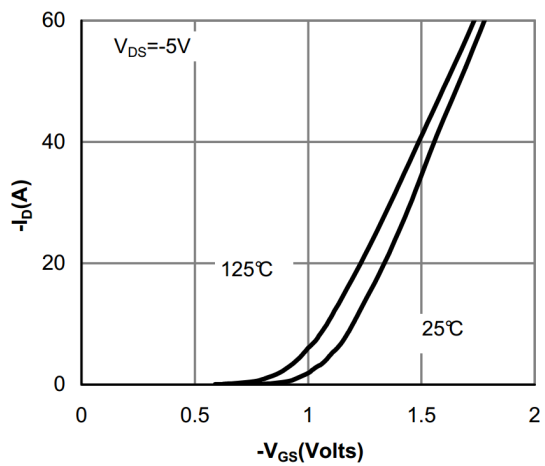


Figure 2: Transfer Characteristics

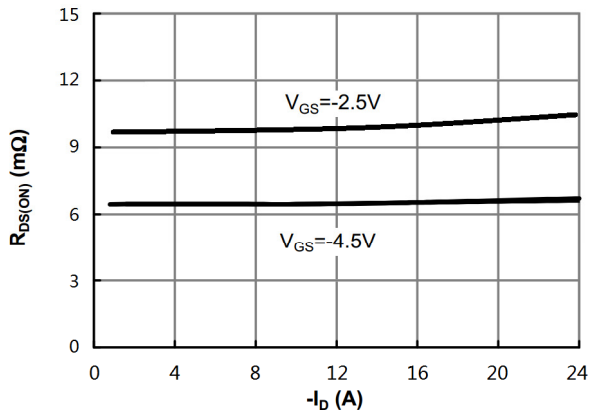


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

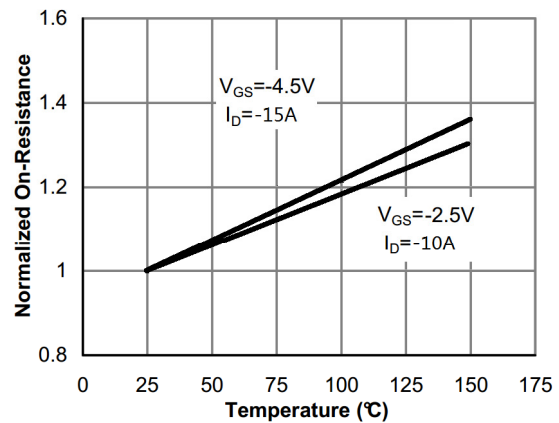


Figure 4: On-Resistance vs. Junction Temperature

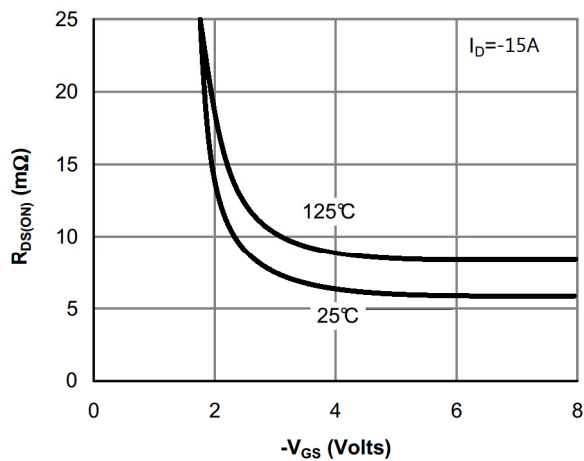


Figure 5: On-Resistance vs. Gate-Source Voltage

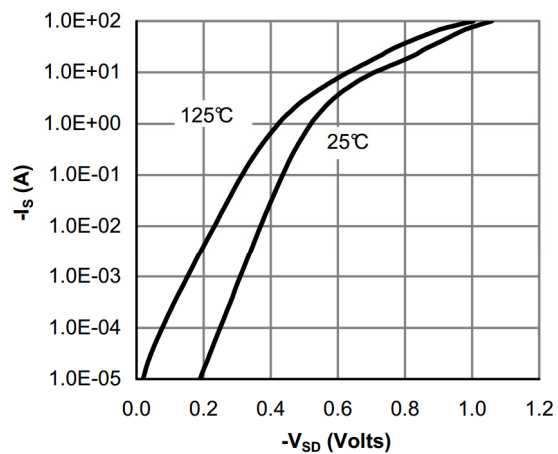


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

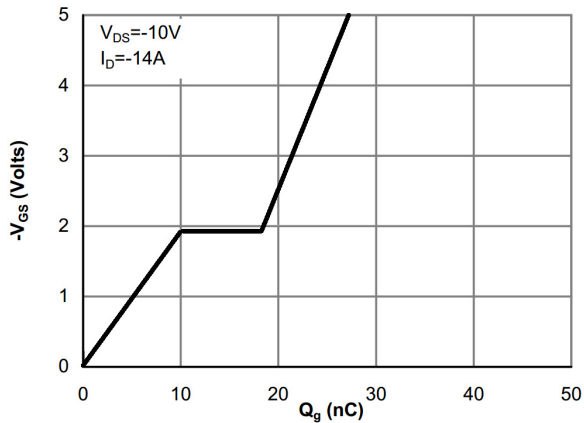


Figure 7: Gate-Charge Characteristics

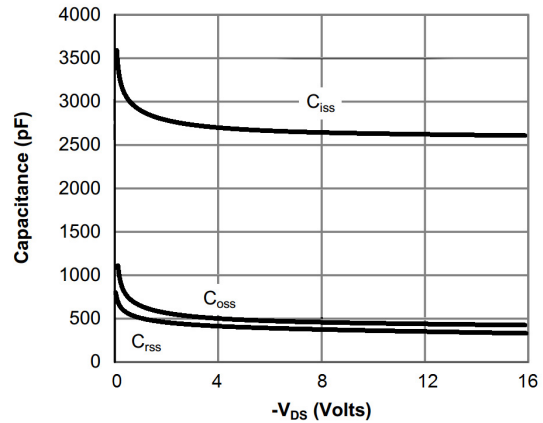


Figure 8: Capacitance Characteristics

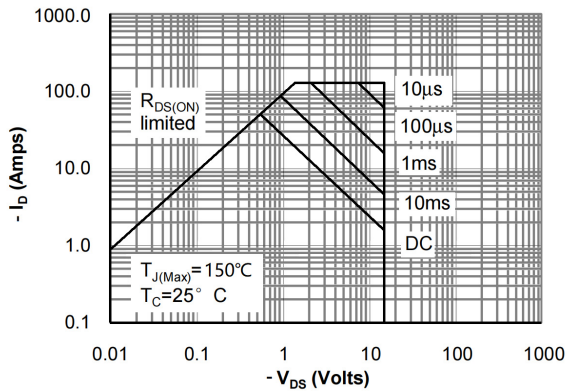


Figure 9: Maximum Forward Biased Safe Operating Area

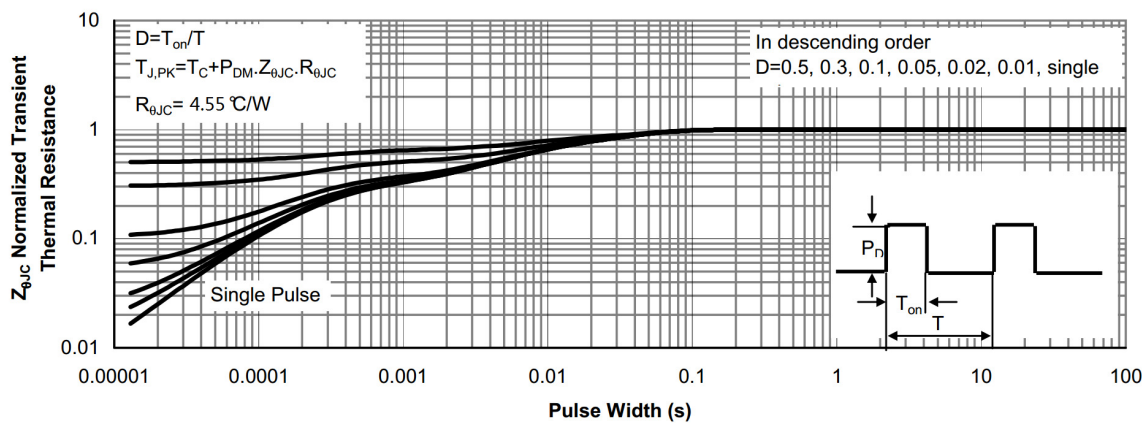
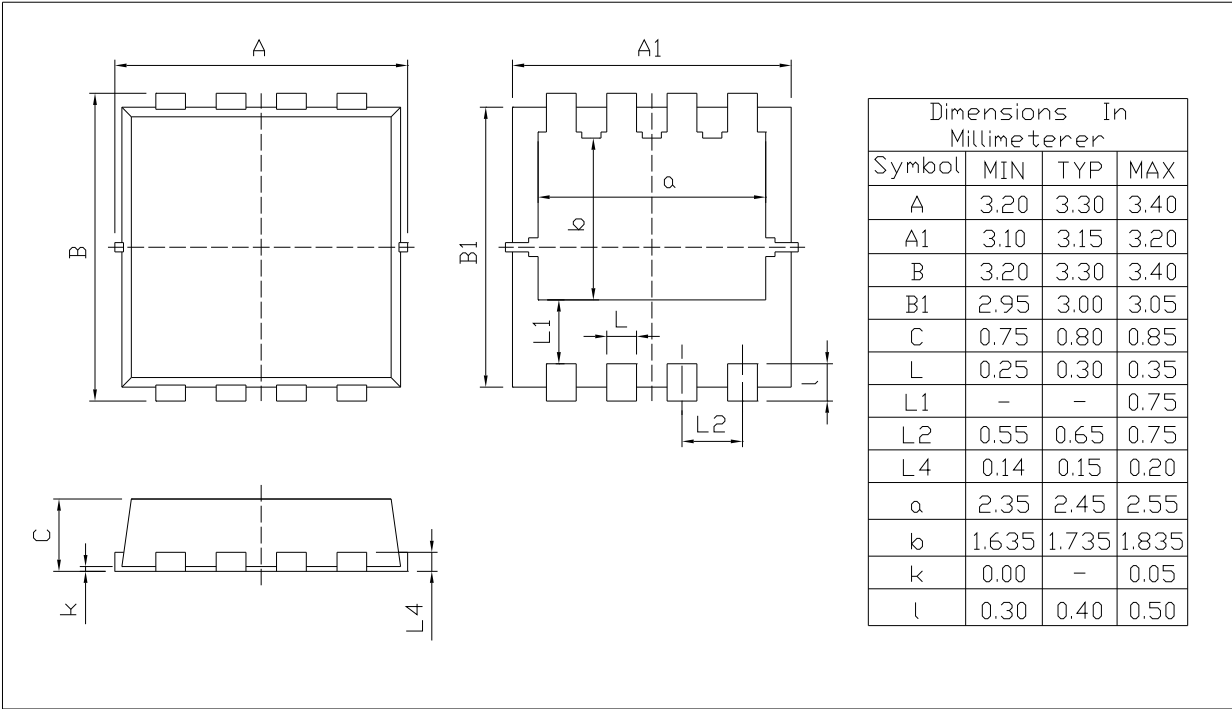


Figure 10: Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

PDFN3X3A-8L

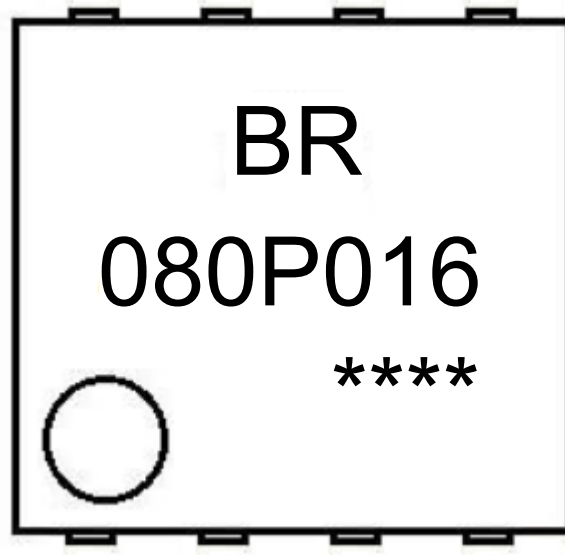
Unit:mm



Rev.00 202011



印章说明 / Marking Instructions



说明：

BR： 为公司代码

080P016： 为型号代码

****： 为生产批号代码，随生产批号变化

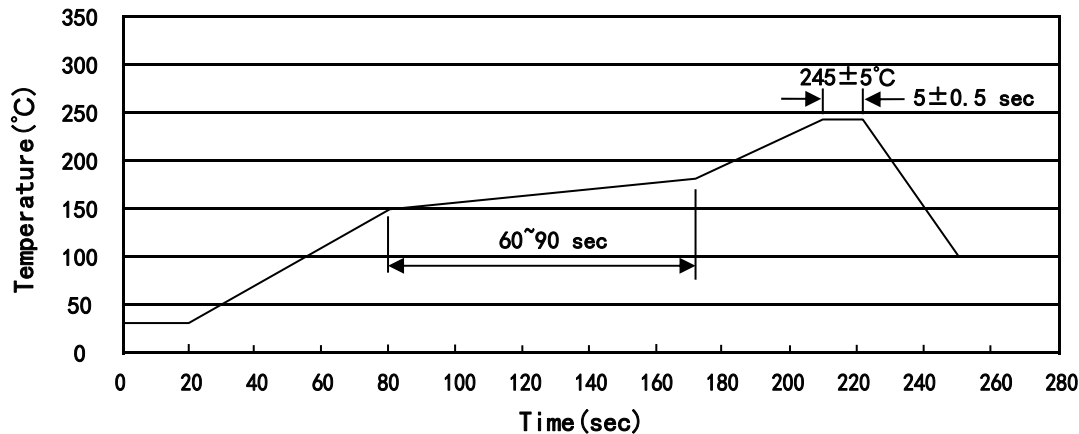
Note:

BR: Company Code

080P016: Product Type Code

****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
PDFN3×3A-8L	5,000	2	10,000	6	60,000	13" ×12	360×360×50	380×335×366

使用说明 / Notices

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